a lest out the semiconductors products for the corresponding \* Products: Microprocessors

Copus for desktop's, laptop, sewers & mobile company: Intel, AMD, ARM, Oudcomm, Apple, NVIDIA. · product: memory (DRAM, NANDflash memory) company: samsung micron technology, tarhibha, werless aproduct: Microcontroller a FPCeAs, REChips, Cous Company's TSMC, Sansung foundry, Intel, AMD, Analog Semi conduitos. product: Amplifier, semiconductors, convertors, voltage regulators, power management Ics Company: TI, Analog device, Marin Interealed products disciele 5 \*products: Imagesensors, temperature sensors, accelarantes gyroscoper. Company Sory, samsong, Bosch, NXP, STmiceoelection rpuducts: power electronics involve Mosfets, IqBTs, power module, involves, converters company: Infinear, Technologier, ON semiconductor o Products: PErcomponents involver et switches,

fillers, Mixers, Oscillators

mpany: 0 Company: Oorro, Skywoods, NXP1 Broadcom.

· products: Optical Components: cers, lossers, photodelactor optical amplifors, optical modulations Company: Samong, La innotate , Broadcan, Ossam. productofrom specefic companies: ·AMD:- They manufacture microprocessors, produces aside same of semiconductor products including graphy Caeds, populs & logic chips · Intel: Intel is a leading manufacture of micoprocon memory, Logic chips · TEMC: TEMC is would's largest foundy manufacture.

Chips for other companies. It is major supplier for

Apple, NNIDIA & Qualcomm. · BOSCH:-Manufactures MFMs devices & sensois. e Qualcomm? Monufactures snapoliagon processors, 54 fua moderns, with bluetooth chips, ettansa Dhly there is a shift from BIT-to Mosfer of Mosfer to FINFET. accessent technology nodes of 8JT = 22nm Mosfet: Anm FINITET: 5 mm. As joucan see there is a degradation of transistan manufacturing integrating on a chip from BIT to Moster & Mosfet To FINFET -> BJTS-to MOSFETS a power efficient focaling:- Mosfet's gained promin-ence over BIT's due to their superior power efficient of scalability. Mosfet's operate on the

principle of vollage control, of leing high ment Impade MOSFET's all smaller in size & has faster switching speeds, making them suitable for high frequency cros technology which became modern integrated cravits, offers low power consumption & also digetal 10 je cucit derign. 2MOSFET'S to FMFET'S: escaling limitations; Mosfel's were stated down to smaller sizer, they face challenger to short-channel effects increasing leakage currents. . Finfets feature a Three-dimensional fin-like structure for the channel, offeig better control Over the channel. providing superior control, reduced leakage

Power & Better ocalability 3) What are the latest laptop processors from AMD, Intel & Apple: frequeny & node? A AMD! . AMD Pyzen a 7000 Seie, DAMD Ryzen 9 7950×3D clock frequery: 4.2 att (Bose clock) "lechnology node : Tomc 5nm FINFET max + clock frequeny: upto 5.74Hz AMD fyten 97945 H x 3D: Baxe clock: 3.7 atit Max Boost clock: upto 549412 Technology mode: TSMC Som finfet.

Intel core of 14th generation Trequency ruple 6.0 GHZ processor family! melear lake Technology rad 5mm procen rode @ Ma prof Ma Moxi-Ma pro--frequery wasto 3.49 CHIZ Tachnology node = 5mm frequency = upto 3549+12 Technologynode = 5 mm. What on the different job ides available is · RTC derignengneu \* Verstalion engineer DFT engineel · 5TA enzineer . physical d'esign engineer · layout engineer. · Analog design engineer Digted derign engineer. · soc Architech · Franderign engineer. 

Evolution of memories. Themony POM 1. SRAM 1. M ROMA 2. ORAM a. PROM B. SDRAM 3. EPROM 4. DDP SDRAM 4. E E R OM 5. GDDR SDRAM 5. Flaghoom. 6. LPDDR 7 Flonk RAM. PSRAM (Static RAM) -robles the afostert accentines of all RAM-year o volatile: l'onerdata when pouce is lost => More expensive 2. DRAM (Pynamic RAM). -> slower than SRAM, used for general purpose apptaling -> den expensive 3. SDRAM (Synchromour RAM). -) Synchronous its operation with the systemchot, enhan -ced data transfer than DRAM. -> widely used. 4. DIDR SRAM (Double Data Rate SRAM): Improved performance, transfer data on both vising is falling edger of the clock signal. Multiple generations each offering different Specifications: Suppr SRAM (Graphics Double Pata Rate SPAM) 2) optimused graphics

81 to Han Standard PPR.

6 LPDDR (Jow-power DDR)-Reduced power consumptions; consumer len pour standy DOR, SDRAM making it suitable for mobile dewices 1 MROM (masked ROM): > oldest & samplest ROM, which is low cost programmed duling the chips -> pata is permanently manufacture 7 Not reprogrammable. @ PROM (programmable ROM): - Data can be programmed once using a special device called a Prom Programmer. I len flexible, used in applications where the data's reslikely to change. (3) EPROM (Erasable programmable ROM):-> Data can be crossed using ultraviolet light & thes (2) EEPROM (Electrically Evarable programmable ROM) -> Data can be crossed & reprogrammed electronicity a Most resatile type of pom. (5) Flash POM: 7-A type of EEPROM. - widely used in USB - flash deriver: sap's (adid state devices) & other storage devices high density, high speeds a low pour Consumplion

6) Mhat au latert mobile processors available from Qualcomm & mediatet: frequez é node. A Qualcoms: · Snapdragon & Gem 3 doct speed (frequeny): 3.3GHZ. procent node of technology = 4nm. · snapdrogen & Cena! Clock speed: 3.3899 HR process-node! unns Mediatek! . Mediatet Dimensity 9300 I clock speed: ux Aron Cortex - xy at 325 GAR ", 4x Aun cotter - A720 upto 2.00Hz Procen node! 30d gen ToMC Unmchip. · Mediatek Dimensity 9200+ -> clock speed: 1x Aun cortex\_23 at 3.354+17. 3× Am contex -A+15 uplo 3. OcHZ. 4x Avn corter - A510 upto 2.0014 -> procen node? unm ToMc chip.